

General Description

The series of devices use advanced trench gate super junction technology and design to provide ultra-low $R_{DS(ON)}$ and low gate charge and With a rapid recovery body diode. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, industrial power applications, Fast charger, new energy vehicle charging pile, on-board OBC etc.

Features

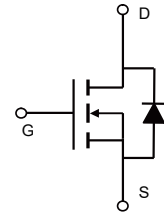
- New technology for high voltage device
- Ultra low on-resistance and ultra low conduction losses
- Ultra Low Gate Charge cause lower driving requirements
- Diode reverse recovery speed is super fast
- High reliability
- ROHS compliant & Halogen Free

Application

- Power factor correction (PFC)
- Switched mode power supplies (SMPS)
- Uninterruptible Power Supply (UPS)
- On-board charger (OBC)



TO-263



Schematic

Parameter	Symbol	Value	Unit
Drain-Source Voltage ($V_{GS}=0V$)	V_{DS}	650	V
Gate-Source Voltage ($V_{DS}=0V$) AC ($f>1$ Hz)	V_{GS}	± 30	V
Gate-Source Voltage ($V_{DS}=0V$) DC	V_{GS}	± 20	V
Continuous Drain Current at $T_c=25^\circ C$	$I_{D(DC)}$	26	A
Continuous Drain Current at $T_c=100^\circ C$	$I_{D(DC)}$	18.2	A
Pulsed drain current (Note 1)	$I_{DM(pluse)}$	78	A
Maximum Power Dissipation ($T_c=25^\circ C$)	P_D	237	W
Derate above $25^\circ C$		1.58	W/ $^\circ C$
Avalanche current (Note 1)	I_{AS}	7	A
Drain Source voltage slope, $V_{DS} \leq 480$ V,	dv/dt	50	V/ns
Reverse diode dv/dt , $V_{DS} \leq 480$ V, $I_{SD} < I_D$	dv/dt	50	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55...+175	$^\circ C$

* limited by maximum junction temperature

Table 2. Thermal Characteristic

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (Maximum)	R_{thJC}	0.63	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient (Maximum)	R_{thJA}	62	$^{\circ}\text{C}/\text{W}$

Table 3. Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250uA	650			V
Zero Gate Voltage Drain Current(Tc=25℃)	I _{DSS}	V _{DS} =650V,V _{GS} =0V			10	μA
Zero Gate Voltage Drain Current(Tc=125℃)	I _{DSS}	V _{DS} =650V,V _{GS} =0V			400	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =500uA	3.5	4.2	5.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =13A		110	130	mΩ
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =50V,V _{GS} =0V, F=1.0MHz		2161		pF
Output Capacitance	C _{oss}			95		pF
Reverse Transfer Capacitance	C _{rss}			1.3		pF
Total Gate Charge	Q _g	V _{DS} =480V,I _D =13A, V _{GS} =10V		41.2		nC
Gate-Source Charge	Q _{gs}			16.3		nC
Gate-Drain Charge	Q _{gd}			12.8		nC
Gate plateau voltage	V _{gp}			7.0		V
Intrinsic gate resistance	R _G	f = 1 MHz open drain		1.5		Ω
Switching times						
Turn-on Delay Time	t _{d(on)}	V _{DD} =380V,I _D =13A, R _G =1.7Ω,V _{GS} =10V		43		nS
Turn-on Rise Time	t _r			16		nS
Turn-Off Delay Time	t _{d(off)}			93		nS
Turn-Off Fall Time	t _f			20		nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I _{SD}	T _C =25℃			26	A
Pulsed Source-drain current(Body Diode)	I _{SDM}				78	A
Forward On Voltage	V _{SD}	T _j =25℃,I _{SD} =26A,V _{GS} =0V		1.0	1.2	V
Reverse Recovery Time	t _{rr}	T _j =25℃,I _F =13A,di/dt=100A/μs		145		nS
Reverse Recovery Charge	Q _{rr}			0.725		uC
Peak Reverse Recovery Current	I _{rm}			10		A

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2. $T_J=25^{\circ}\text{C}, V_{DD}=50V, V_G=10V, R_G=25\Omega$

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

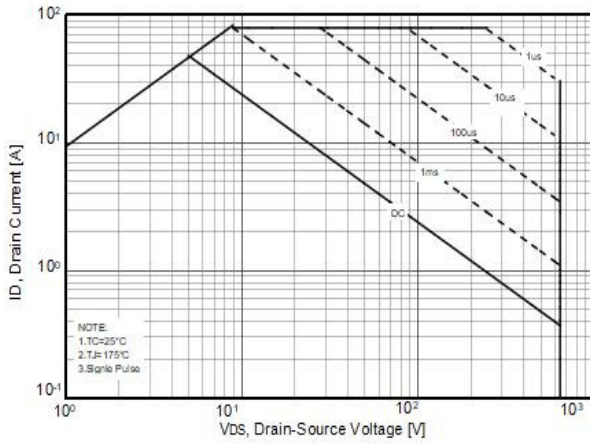
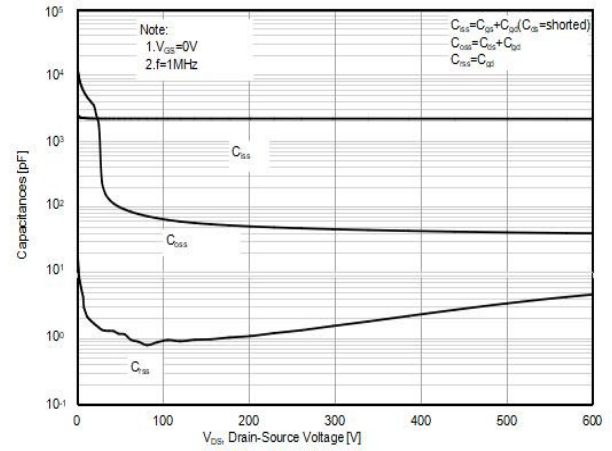
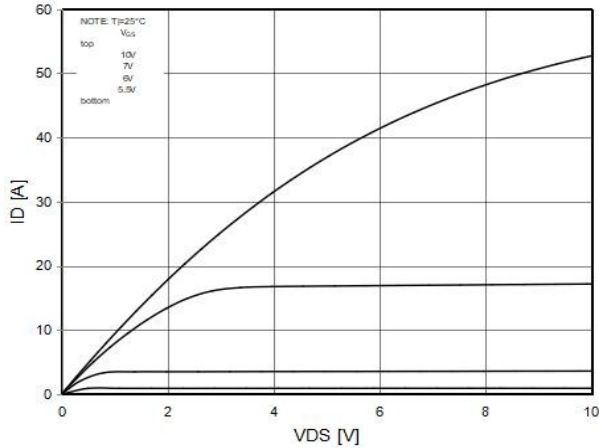
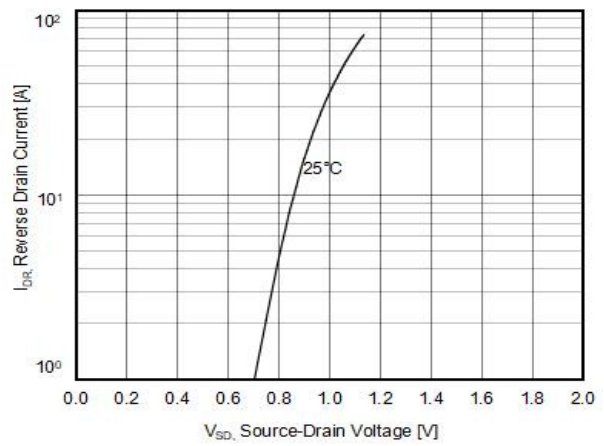
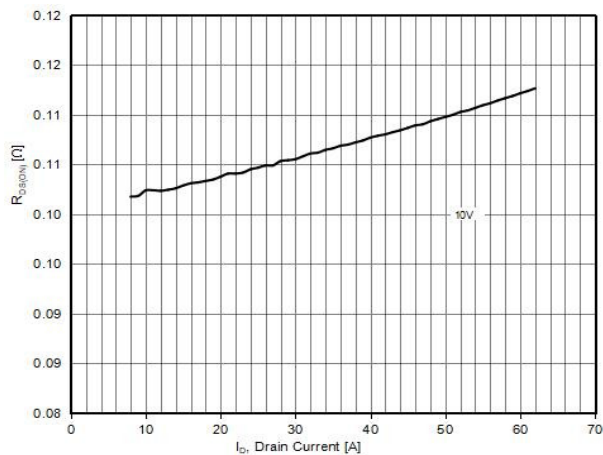
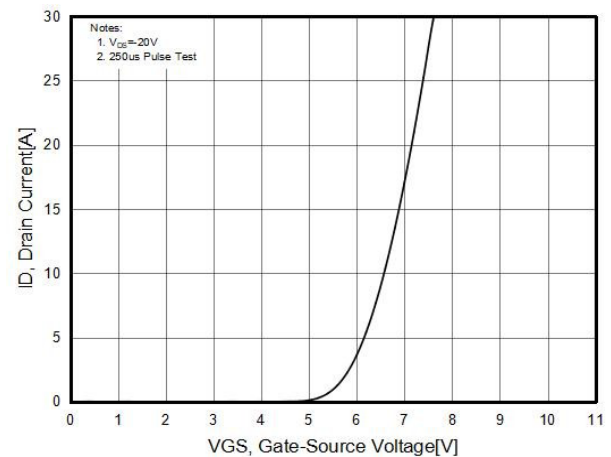
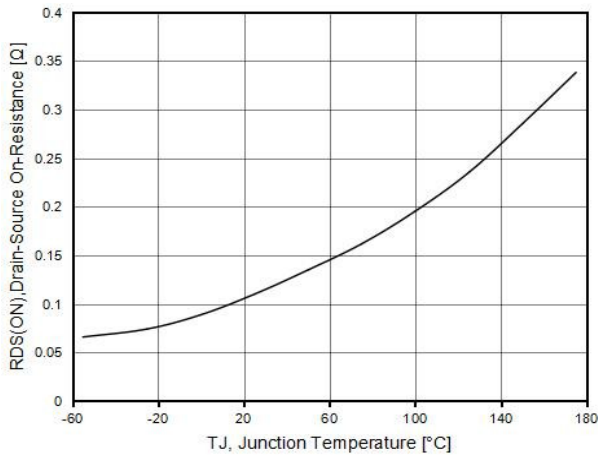
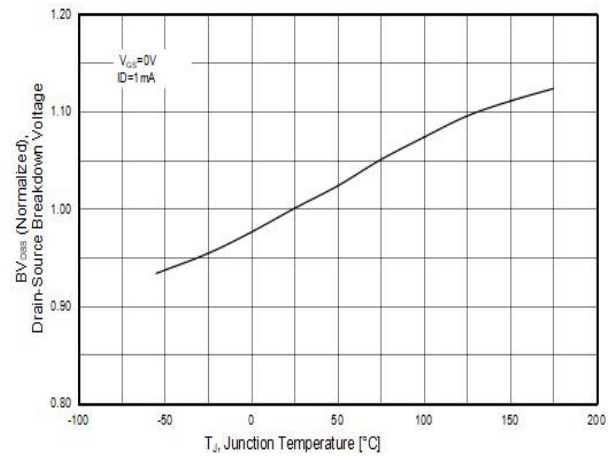
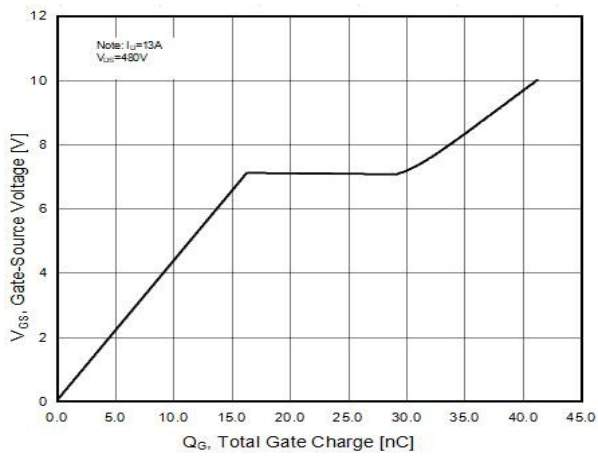
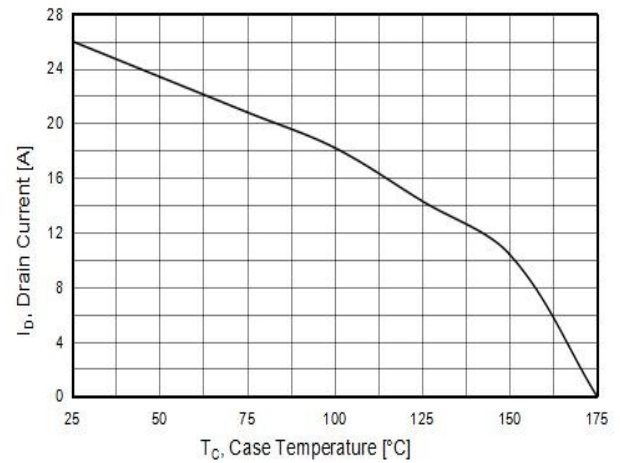
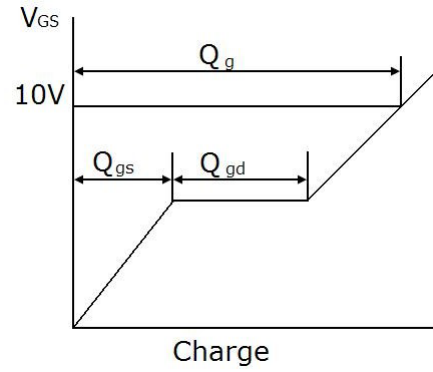
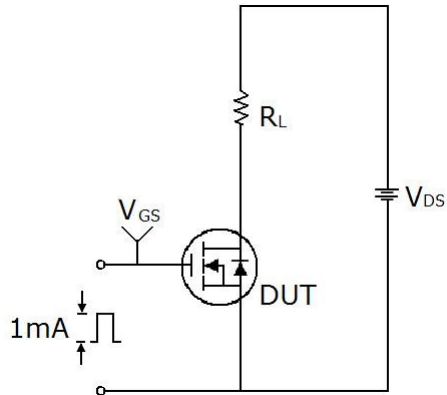
Figure1. Safe operating area

Figure2. Capacitance

Figure3. Output characteristics

Figure4. Source-Drain Diode Forward Voltage

Figure5. Static drain-source on resistance

Figure6. Transfer characteristics


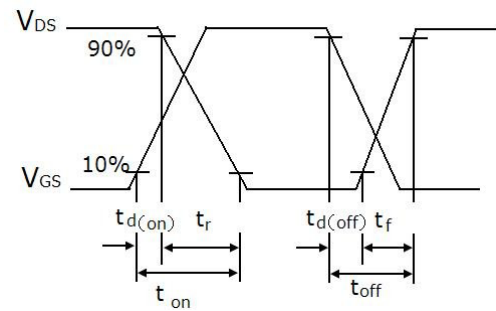
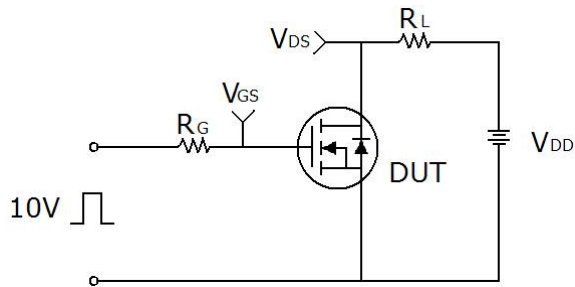
Figure7. $R_{DS(ON)}$ vs Junction Temperature

Figure8. BV_{DSS} vs Junction Temperature

Figure9. Gate charge waveforms

Figure10. Maximum I_D vs Junction Temperature


Test circuit

1) Gate charge test circuit & Waveform



2) Switch Time Test Circuit:



3) Unclamped Inductive Switching Test Circuit & Waveforms

